

DMA2610F

Silicon PNP epitaxial planar type

For digital circuits

■ Features

- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

■ Basic Part Number

Dual DRA2143X (Common emitter)

■ Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-50	V
Collector-emitter voltage (Base open)	V_{CEO}	-50	V
Collector current	I_{C}	-100	mA
Total power dissipation	P_{T}	300	mW
Junction temperature	T_{j}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_{\text{C}} = -10 \mu\text{A}, I_{\text{E}} = 0$	-50			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_{\text{C}} = -2 \text{ mA}, I_{\text{B}} = 0$	-50			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{\text{CB}} = -50 \text{ V}, I_{\text{E}} = 0$			-0.1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{\text{CE}} = -50 \text{ V}, I_{\text{B}} = 0$			-0.5	μA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{\text{EB}} = -6 \text{ V}, I_{\text{C}} = 0$			-1.0	mA
Forward current transfer ratio	h_{FE}	$V_{\text{CE}} = -10 \text{ V}, I_{\text{C}} = -5 \text{ mA}$	30			—
h_{FE} ratio *	h_{FE} (Small/Large)	$V_{\text{CE}} = -10 \text{ V}, I_{\text{C}} = -5 \text{ mA}$	0.50	0.99		—
Collector-emitter saturation voltage	$V_{\text{CE(sat)}}$	$I_{\text{C}} = -10 \text{ mA}, I_{\text{B}} = -0.5 \text{ mA}$			-0.25	V
Input voltage (ON)	$V_{\text{I(on)}}$	$V_{\text{CE}} = -0.2 \text{ V}, I_{\text{C}} = -5 \text{ mA}$	-1.7			V
Input voltage (OFF)	$V_{\text{I(off)}}$	$V_{\text{CE}} = -5 \text{ V}, I_{\text{C}} = -100 \mu\text{A}$			-0.6	V
Input resistance	R_1		-30%	4.7	+30%	k Ω
Resistance ratio	R_1 / R_2		0.37	0.47	0.57	—

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Ratio between 2 elements

■ Package

• Code

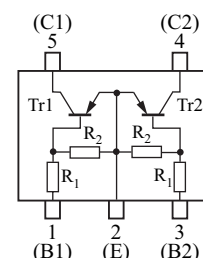
Mini5-G3-B

• Pin Name

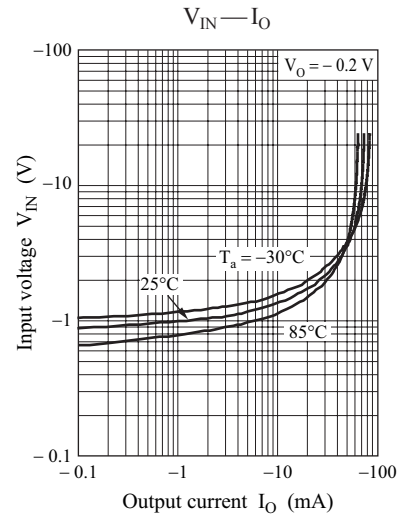
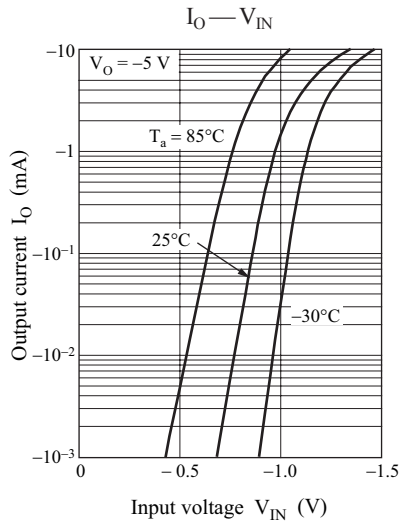
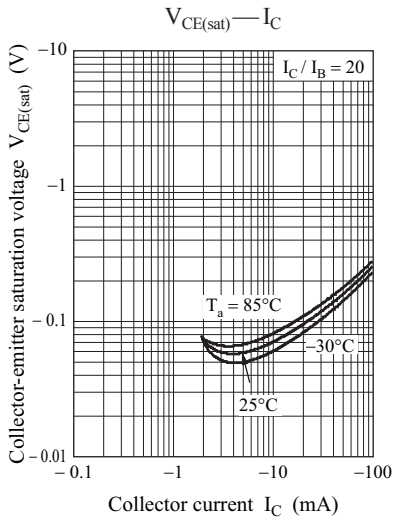
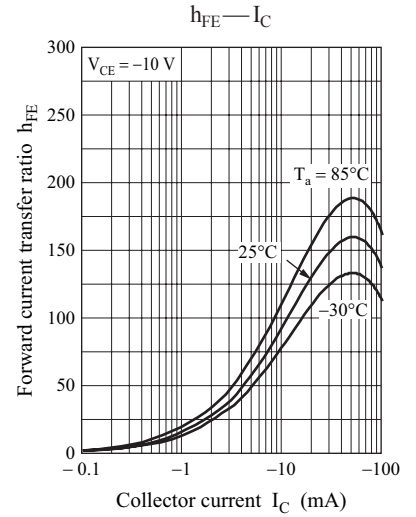
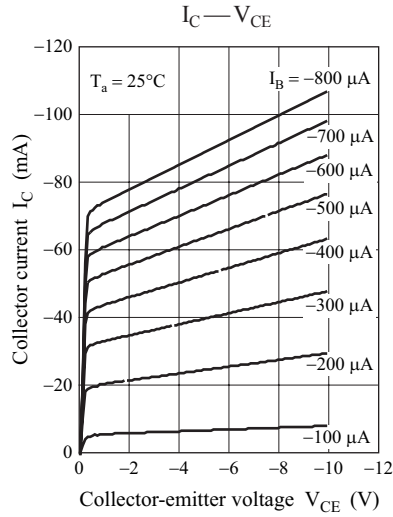
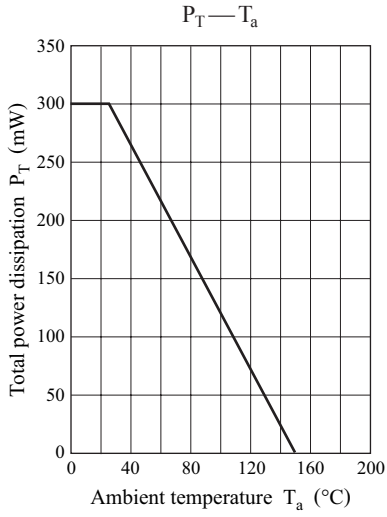
- 1: Base (Tr1) 4: Collector (Tr2)
- 2: Emitter (Common) 5: Collector (Tr1)
- 3: Base (Tr2)

■ Marking Symbol: R3

■ Internal Connection

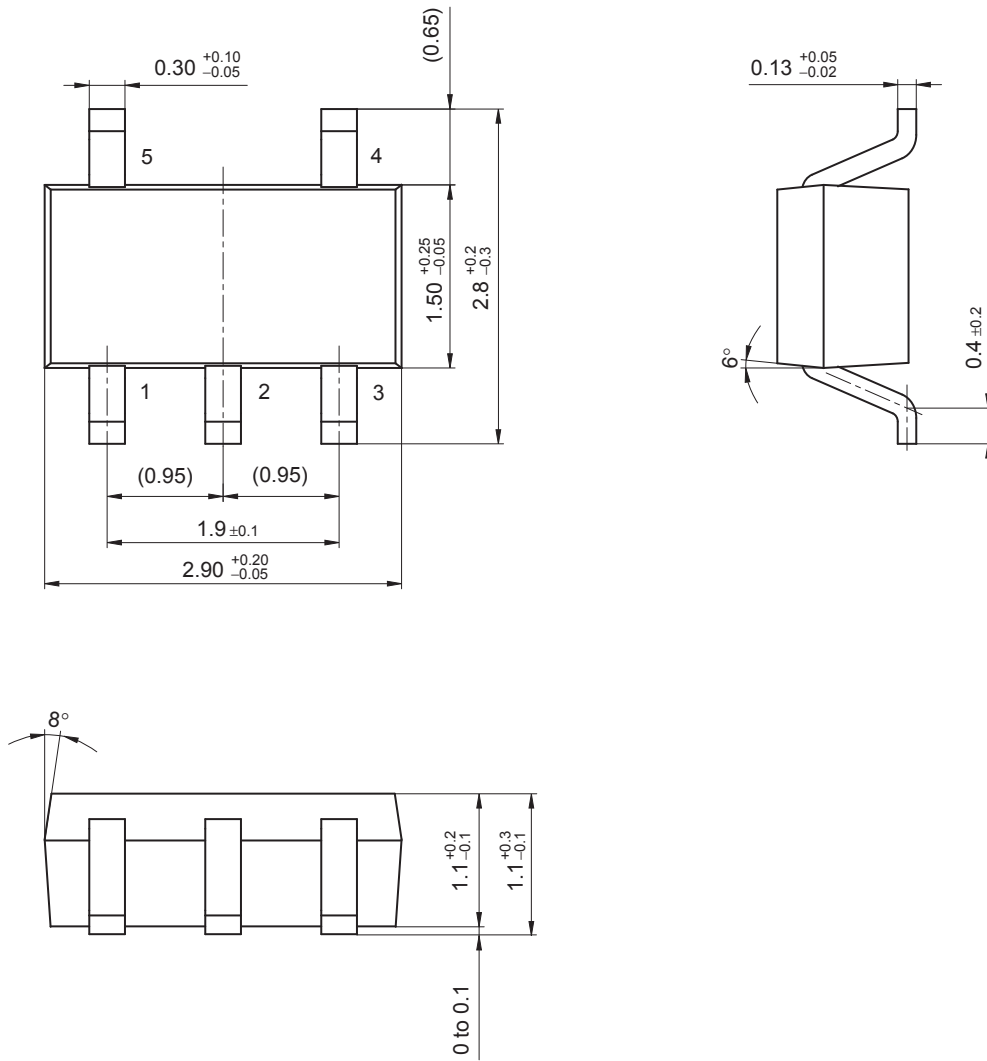


Resistance value	R_1	4.7	k Ω
	R_2	10	k Ω



Mini5-G3-B

Unit: mm



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